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# **MBR260HW SCHOTTKY RECTIFIER**

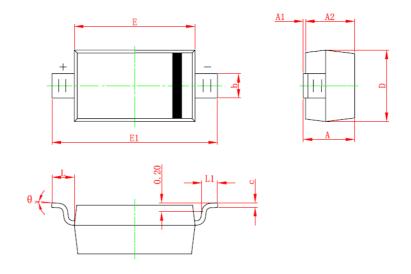
## **Applications:**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

### Features:

- 125 ℃ TJ operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- . Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Mechanical Dimensions (In mm/Inches)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
С	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

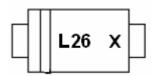
### **SOD-123**





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## **Marking Diagram:**



Where X is Date Code

L26 = Part Name

Cautions: Molding resin

Epoxy resin UL:94V-0

# **Ordering Information:**

Device	Package	Shipping
MBR260HW	SOD-123 (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

<sup>•</sup> FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



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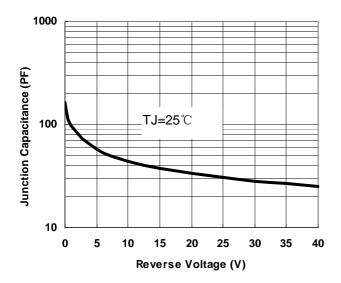
# Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25℃ unless otherwise specified

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	60	V
Average Rectified Forward Current (At Rated VR, TL = 55°C)	lo	2	А
Forward Voltage $@I_F = 1A, T_A = 25$ °C $@I_F = 2A, T_A = 25$ °C	$V_{FM}$	0.52 0.66	V
Peak Reverse Current @T <sub>A</sub> = 25℃	I <sub>RM</sub>	50	μА
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half-wave, Single Phase, 60 Hz)	IFSM	30	А
Maximum Junction Capacitance (Note 1)	Cj	100	pF
Operating Junction Temperature Range	TJ	125	G
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	C
Approximate Weight	wt	0.028	g
Case Style	SOD-123		

Note 1. Measured at 1MHz and applied reverse voltage of 5.0V D.C.

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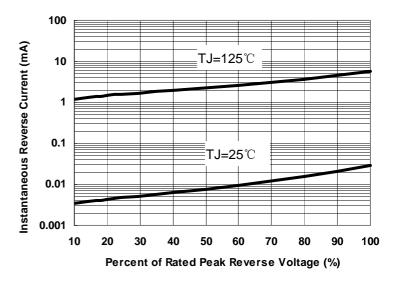


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

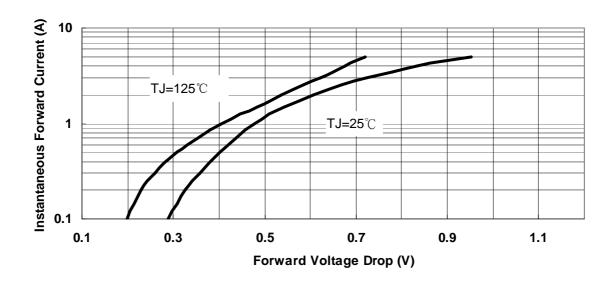


Fig.3-Typical Forward Voltage Drop Characteristics

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## MBR260HW

Technical Data Data Sheet N1503, Rev. A **Green Products** 

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